

### Abstract of the Disclosure

A method for manufacturing an FeRAM capacitor is employed to enhance an adhesive property between a dielectric layer and a first bottom electrode of iridium. The method including the steps of: preparing an active matrix including a semiconductor substrate, a transistor, a bit line, a first ILD, a second ILD and a storage node; forming a first bottom electrode on the second ILD and the storage node; forming a third ILD on exposed surfaces of the first bottom electrode and the second ILD; planarizing the third ILD till a top face of the first bottom electrode is exposed; forming a second bottom electrode on the top face of the bottom electrode; forming conductive oxides on exposed sidewalls of the first bottom electrode by carrying out an oxidation process; forming a dielectric layer on exposed surfaces of the first bottom electrodes, the second bottom electrode and the second ILD; and forming a top electrode on the dielectric layer.